

# **isc Silicon NPN Power Transistor**

# 3DD104D

#### **DESCRIPTION**

- · With TO-3 packaging
- Large collector current
- · Low collector saturation voltage
- · High power dissipation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



### **APPLICATIONS**

- Designed for use in DC-DC converter
- · Driver of solenoid or motor

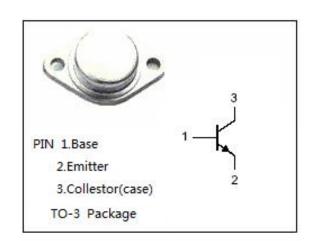


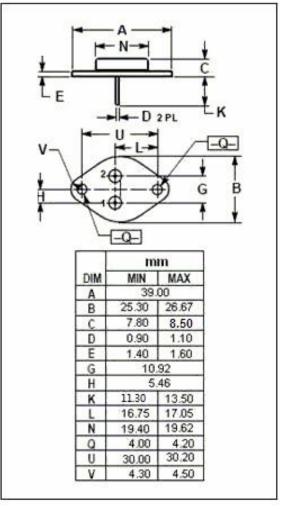
# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL           | PARAMETER                       | VALUE   | UNIT       |
|------------------|---------------------------------|---------|------------|
| $V_{CBO}$        | Collector-Base Voltage          | 1200    | V          |
| V <sub>CEO</sub> | Collector-Emitter Voltage       | 600     | V          |
| V <sub>EBO</sub> | Emitter-Base Voltage            | 8       | V          |
| Ic               | Collector Current-Continuous    | 3       | А          |
| P <sub>D</sub>   | Total Power Dissipation@Tc=75°C | 50      | W          |
| TJ               | Max.Junction Temperature 175    |         | $^{\circ}$ |
| T <sub>stg</sub> | Storage Temperature             | -55~175 | $^{\circ}$ |

### THERMAL CHARACTERISTICS

| SYMBOL              | PARAMETER                           | MAX | UNIT |
|---------------------|-------------------------------------|-----|------|
| R <sub>th j-c</sub> | Thermal Resistance,Junction to Case | 2.0 | °C/W |







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

| SYMBOL               | PARAMETER                            | CONDITIONS                                 | MIN  | MAX | UNIT |
|----------------------|--------------------------------------|--|------|-----|------|
| BV <sub>CEO</sub>    | Collector-Emitter Sustaining Voltage | I <sub>C</sub> = 5mA; I <sub>B</sub> = 0   | 600  |     | V    |
| BV <sub>CBO</sub>    | Collector-Base Sustaining Voltage    | I <sub>C</sub> = 5mA; I <sub>E</sub> = 0   | 1200 |     | V    |
| BV <sub>EBO</sub>    | Emitter-Base Sustaining Voltage      | I <sub>E</sub> = 5mA; I <sub>C</sub> = 0   | 8    |     | V    |
| V <sub>CE(sat)</sub> | Collector-Emitter Saturation Voltage | I <sub>C</sub> = 3A; I <sub>B</sub> = 1A   |      | 4   | V    |
| І <sub>СВО</sub>     | Collector Cutoff Current             | V <sub>CB</sub> = 500V; I <sub>E</sub> = 0 |      | 0.1 | mA   |
| h <sub>FE</sub>      | DC Current Gain                      | Ic= 1.5A; V <sub>CE</sub> = 10V            | 10   |     |      |



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